

6N135/6N136

General Purpose Type Photocoupler

■ Features

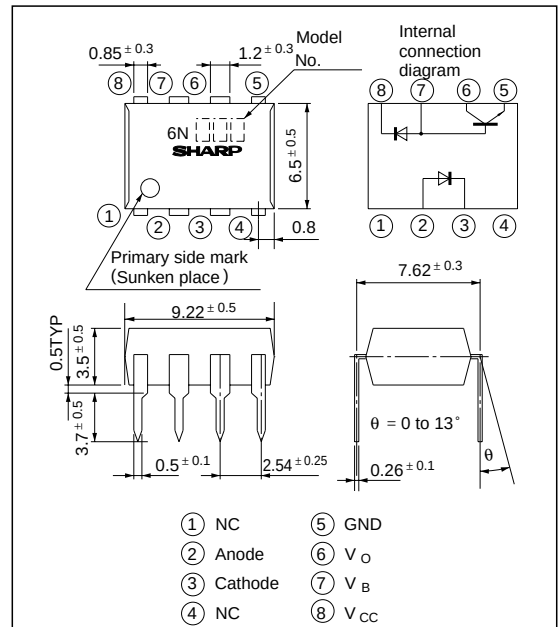
1. High speed response t_{PHL} , t_{PLH}
(**6N135** : MAX. $1.5\mu s$ at $R_L = 4.1k\Omega$)
(**6N136** : MAX. $0.8\mu s$ at $R_L = 1.9k\Omega$)
2. High common mode rejection voltage
(CM_H : TYP. $1kV/\mu s$)
3. Standard dual-in-line package
4. Recognized by UL, file No. E64380

■ Applications

1. Computers, measuring instruments, control equipment
2. High speed line receivers, high speed logic
3. Telephone sets
4. Signal transmission between circuits of different potentials and impedances

■ Outline Dimensions

(Unit : mm)



■ Absolute Maximum Ratings

(Ta = 25°C)

	Parameter	Symbol	Rating	Unit
Input	Forward current	I_F	25	mA
	*1 Peak forward current	I_F	50	mA
	*2 Peak transient forward current	I_{FM}	1	A
	Reverse voltage	V_R	5	V
	Power dissipation	P	45	mW
Output	Supply voltage	V_{CC}	- 0.5 to + 15	V
	Output voltage	V_O	- 0.5 to + 15	V
	Emitter-base reverse withstand voltage (Pin 5 to 7)	V_{EBO}	5	V
	Average output current	I_O	8	mA
	Peak output current	I_{OP}	16	mA
	Base current (Pin 7)	I_B	5	mA
	Power dissipation	P_O	100	mW
	*3 Isolation voltage	V_{iso}	2 500	V_{rms}
	Operating temperature	T_{opr}	- 55 to + 100	°C
	Storage temperature	T_{stg}	- 55 to + 125	°C
	*4 Soldering temperature	T_{sol}	260	°C

*1 50% duty cycle, Pulse width : 1ms

Decreases at the rate of $1.6mA/^\circ C$ if the external temperature is $70^\circ C$ or more.*2 Pulse width $\leq 1\mu s$, 300 p/s

*3 40 to 60% RH, AC for 1 minute

*4 For 10 seconds

* "OPIC" (Optical IC) is a trademark of the SHARP Corporation.

An OPIC consists of a light-detecting element and signal-processing circuit integrated onto a single chip.

■ Electro-optical Characteristics

(Ta = 0 to + 70 °C unless otherwise specified)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
*5Current transfer ratio	6N135	CTR(1)	7.0	40	-	%
	6N136	CTR(1)				
	6N135	CTR(2)	5.0	43	-	%
	6N136	CTR(2)				
Logic (0) output voltage	V _{OL}	*7I _F = 16mA, V _{CC} = 4.5V	-	0.1	0.4	V
Logic (1) output current	I _{OH} (1)	T _a = 25 °C, I _F = 0 V _{CC} = V _O = 5.5V	-	3.0	500	nA
	I _{OH} (2)	T _a = 25 °C, I _F = 0 V _{CC} = V _O = 15V	-	0.01	1.0	μA
	I _{OH} (3)	I _F = 0, V _{CC} = V _O = 15V	-	-	50	μA
Logic (0) supply current	I _{CCL}	I _F = 16mA, V _{CC} = 15V V _O = open	-	200	-	μA
Logic (1) supply current	I _{CCH} (1)	T _a = 25 °C, V _{CC} = 15V V _F = open, I _O = 0	-	0.02	1.0	μA
	I _{CCH} (2)	V _{CC} = 15V V _O = open, I _F = 0	-	-	2.0	μA
Input forward voltage	V _F	T _a = 25 °C, I _F = 16mA	-	1.7	1.95	V
Input forward voltage temperature coefficient	ΔV _F / ΔT _a	I _F = 16mA	-	-1.9	-	mV/°C
Input reverse voltage	BV _R	T _a = 25 °C, I _R = 10 μA	5.0	-	-	V
Input capacitance	C _{IN}	V _F = 0, f = 1MHz	-	60	-	pF
*6Leak current (input-output)	I _{I-O}	T _a = 25 °C, 45 % RH, t = 5s V _{I-O} = 3kVDC	-	-	1.0	μA
*6Isolation resistance (input-output)	R _{I-O}	V _{I-O} = 500VDC	-	10 ¹²	-	Ω
*6Capacitance (input-output)	C _{I-O}	f = 1MHz	-	0.6	-	pF
Transistor current amplification factor	h _{FE}	V _O = 5V, I _O = 3mA	-	70	-	

*5 Current transfer ratio is the ratio of input current and output current expressed in % .

Note) Typical value : at Ta = 25 °C

*6 Measured as 2-pin element (Short 1, 2, 3, 4)

*7 **6N135** : I_O = 1.1mA, **6N136** : I_O = 2.4mA

Fig. 1 Forward Current vs. Ambient Temperature

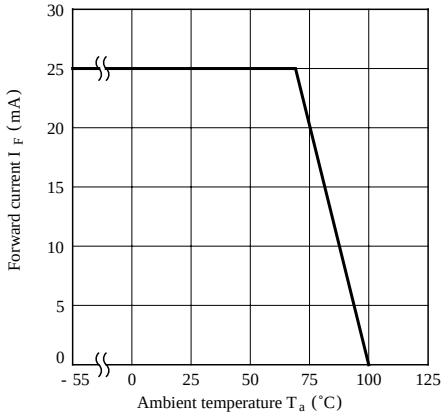


Fig. 2 Power Dissipation vs. Ambient Temperature

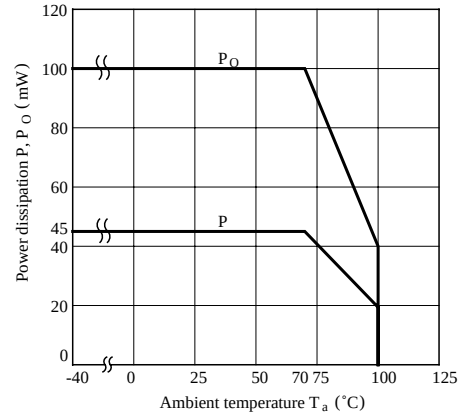


Fig. 3 Forward Current vs. Forward Voltage

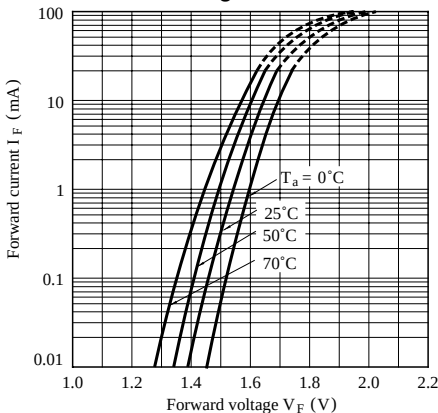


Fig. 4 Relative Current Transfer Ratio vs. Forward Current

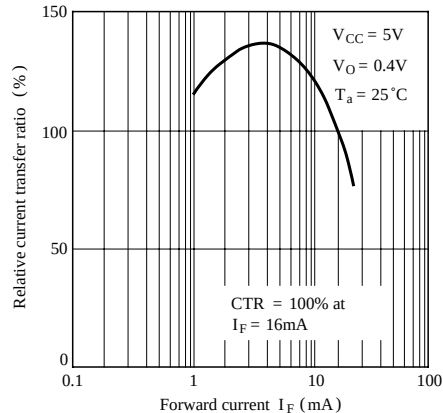


Fig. 5 Output Current vs. Output Voltage

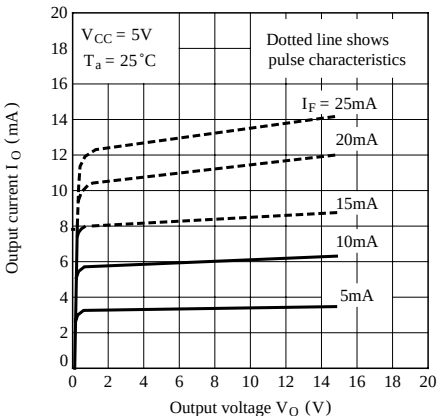


Fig. 6 Relative Current Transfer Ratio vs. Ambient Temperature

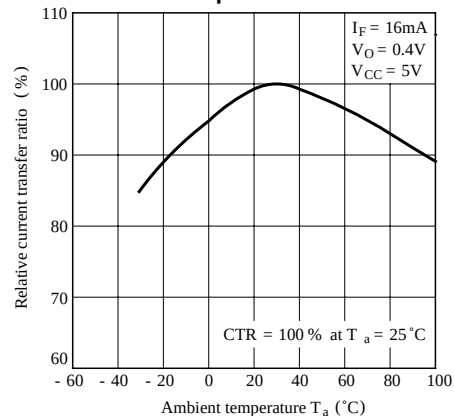


Fig. 7 Propagation Delay Time vs. Ambient Temperature

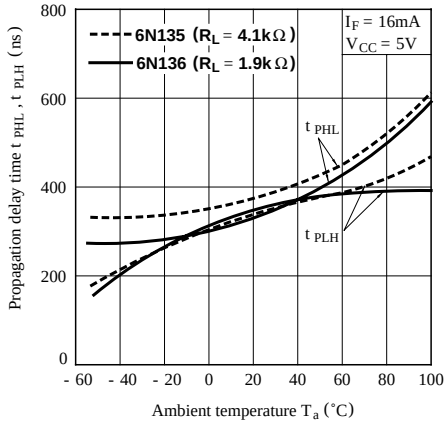


Fig. 8 High Level Output Current vs. Ambient Temperature

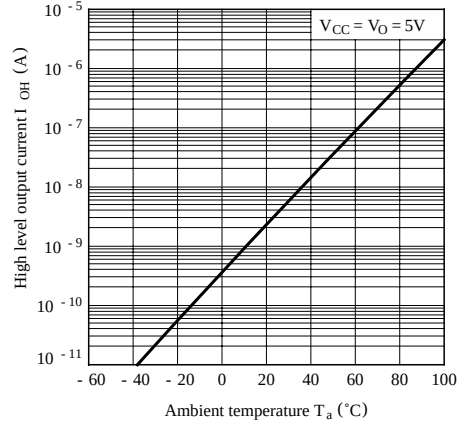
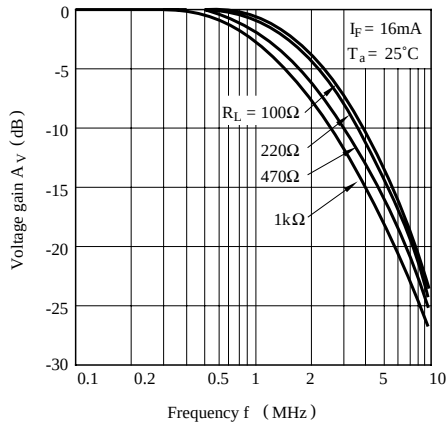
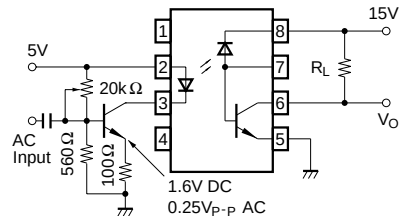


Fig. 9 Frequency Response



Test Circuit for Frequency Characteristic



■ Precautions for Use

- (1) It is recommended that a by-pass capacitor of more than $0.01\mu\text{F}$ be added between V_{CC} and GND near the device in order to stabilize power supply line.
 - (2) Transistor of detector side in bipolar configuration is apt to be affected by static electricity for its minute design. When handling them, general counterplan against static electricity should be taken to avoid breakdown of devices or degradation of characteristics.
- As for other general cautions, please refer to the chapter “Precautions for Use”.
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